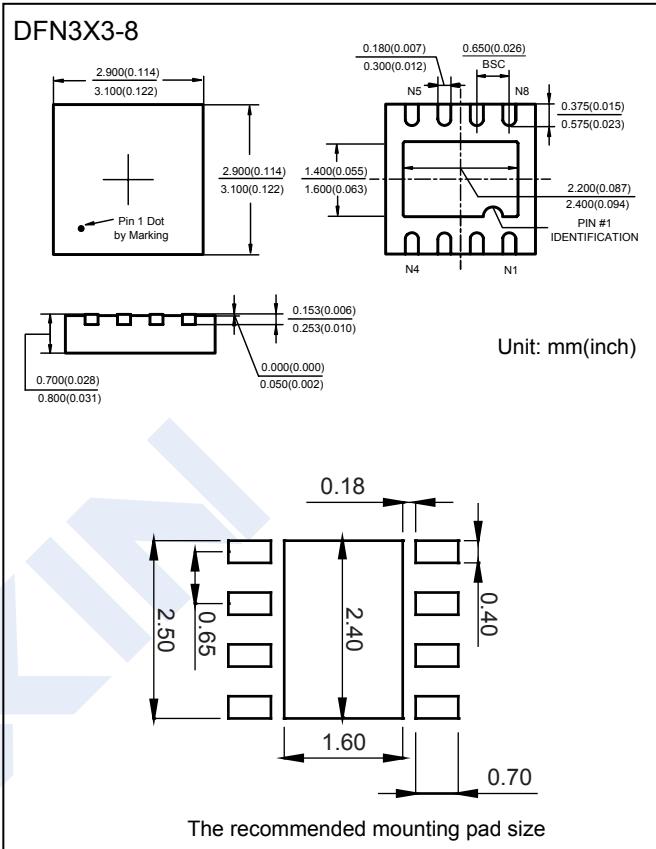
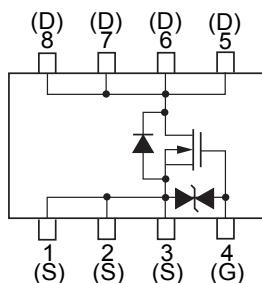


## N-Channel MOSFET

## FK8V03040

## ■ Features

- $V_{DS}$  ( $V$ ) = 33V
- $I_D$  = 10 A ( $V_{GS}$  = 10V)
- $R_{DS(ON)} < 10\text{m}\Omega$  ( $V_{GS}$  = 10V)
- $R_{DS(ON)} < 19\text{m}\Omega$  ( $V_{GS}$  = 4.5V)
- High-speed switching :  $Q_g$  = 7.2 nC

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	33	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current	$I_D$	10	A
		12	
Pulsed Drain Current	$I_{DM}$	40	W
Power Dissipation	$P_D$	1	
		1.5	
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Operating Ambient Temperature	$T_{opr}$	-40 to 85	
Storage Temperature Range	$T_{stg}$	-55 to 150	

## N-Channel MOSFET

### FK8V03040

#### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V <sub>DSS</sub>	I <sub>D</sub> =1 mA, V <sub>GS</sub> =0V	33			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =33V, V <sub>GS</sub> =0V			10	uA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±16V			±10	uA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1.12mA	1		2.5	V
Static Drain-Source On-Resistance	R <sub>Ds(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =5A			10	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A			19	
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =10V, f=1MHz		750		pF
Output Capacitance	C <sub>oss</sub>			170		
Reverse Transfer Capacitance	C <sub>rss</sub>			100		
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =0 to 4.5V, V <sub>DS</sub> =15V, I <sub>D</sub> =10A		7.2		nC
Gate Source Charge	Q <sub>gs</sub>			2.3		
Gate Drain Charge	Q <sub>gd</sub>			3.3		
Turn-On DelayTime	t <sub>d(on)</sub>	V <sub>GS</sub> =0 to 10V, V <sub>DS</sub> =15V, I <sub>D</sub> =5A		9		ns
Turn-On Rise Time	t <sub>r</sub>			6		
Turn-Off DelayTime	t <sub>d(off)</sub>	V <sub>GS</sub> =10 to 0 V, V <sub>DS</sub> =15V, I <sub>D</sub> =5A		46		
Turn-Off Fall Time	t <sub>f</sub>			18		
Maximum Body-Diode Continuous Current	I <sub>S</sub>				10	A
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =5A, V <sub>GS</sub> =0V			1.2	V

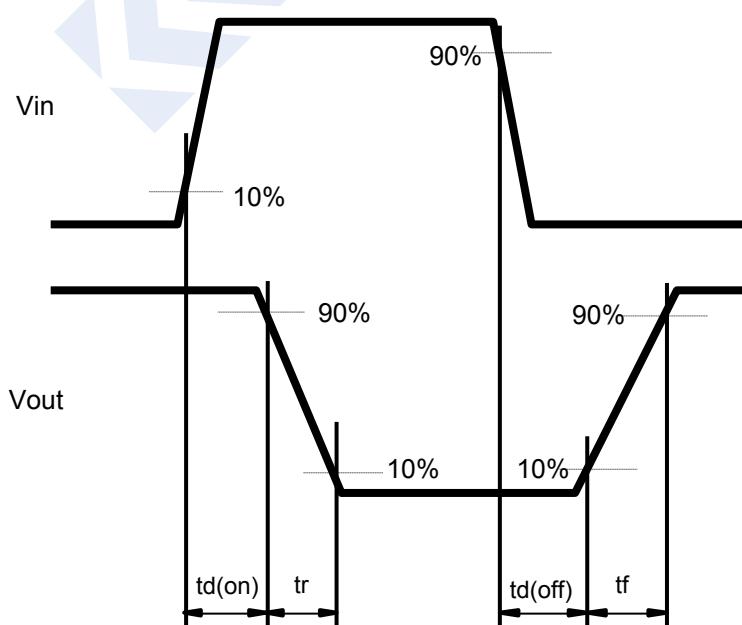
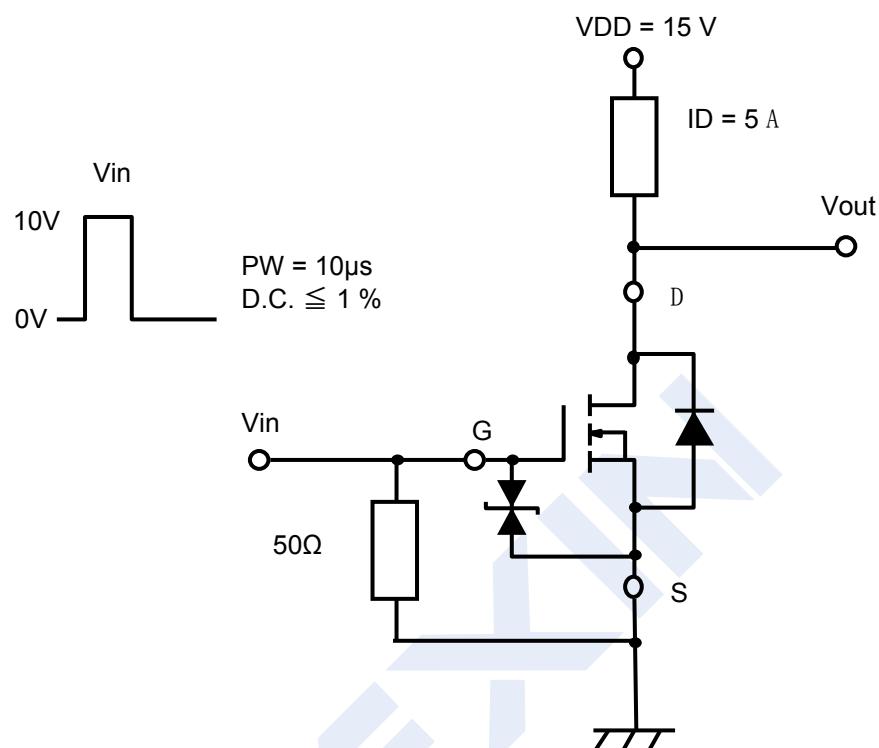
#### ■ Marking

Marking	3D
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## N-Channel MOSFET

### FK8V03040

#### ■ Typical Characteristics

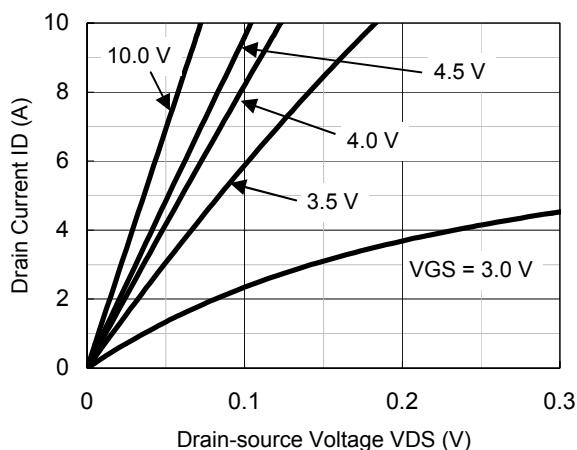


## N-Channel MOSFET

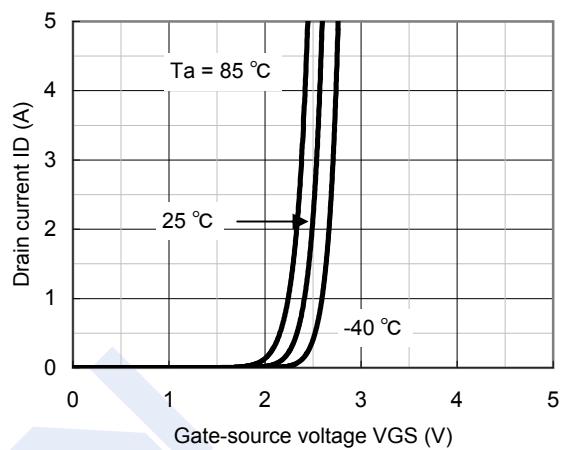
### FK8V03040

#### ■ Typical Characteristics

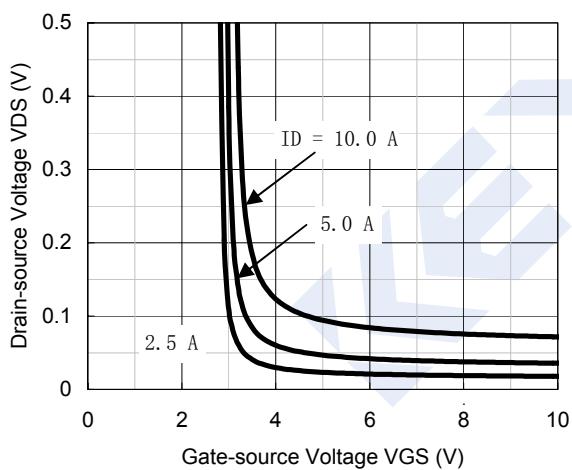
ID - VDS



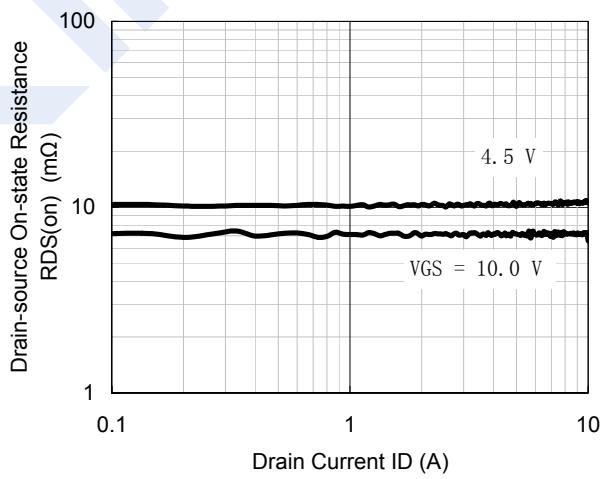
ID - VGS



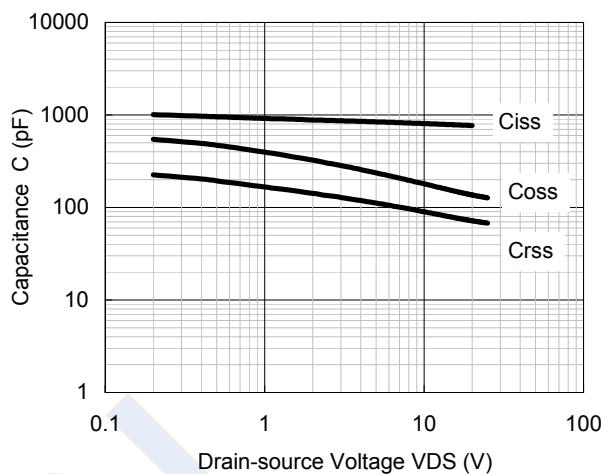
VDS - VGS



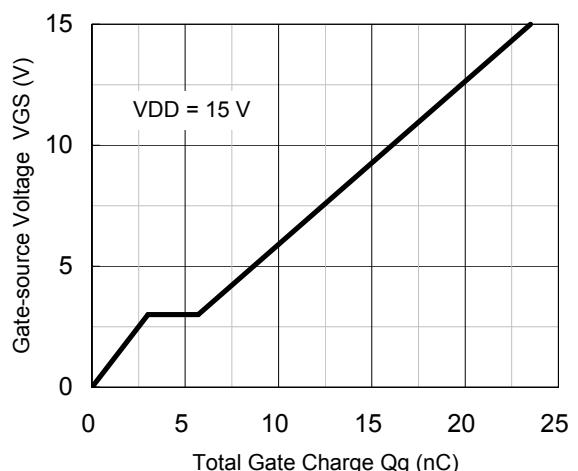
RDS(on) - ID



Capacitance - VDS



Dynamic Input/Output Characteristics



## N-Channel MOSFET

FK8V03040

## ■ Typical Characteristics

